

招聘启事

特拉华大学地处美国东海岸，座落于特拉华州，是美国第一州，也是免税州之一。在美国费城旁边，而且离美国首府华盛顿非常近，约一个半小时车程。

特拉华大学(University of Delaware)工程排名前 50 名，拥有世界先进的纳米加工设备。其电子工程系(Department of Electrical and Computer Engineering) 纳米与微电子专业(Nanoelectronics and microelectronics)正在招收一名博士生和一名博士后，有意者请与曾毓萍教授联系(Advanced Compound Semiconductor Device Group)。

Email 地址: yzeng@udel.edu 倾向有材料，半导体物理与器件基础和相关经验的优秀学生，择优考虑有半导体器件加工制作及集成线路基础经验人才。

要求工作努力，上进，工作自主性强。

博士生待遇: US\$26000 (免学费) 博士后待遇: US\$47,476 with full benefits

工作方向选项:

(1)高频电子器件: 双异质结晶体管, 高电子迁移率晶体管 (heterojunction bipolar transistors and high electron mobility transistors);

(2)低功耗器件: novel transistors (tunneling field effect transistors and III-V metal-oxide-semiconductor field effect transistors);

(3) 发光器件及高速探测器: light emitting diodes, laser diodes, photodetectors, etc.

Prof. Yuping Zeng joined the ECE faculty of University of Delaware in fall 2016. She was one of 20 students selected to Jilin University at the age of 15 for a precocious university program in China, obtaining her B.S. before she was 19. She obtained her M.S. from the National University of Singapore where her main research focused on nanoscale material processes and characterization. She then received her Ph.D. from the Swiss Federal Institute of Technology where she worked with Prof. Colombo Bolognesi on optimizing the design and fabrication process of high speed InP/GaAsSb double heterojunction bipolar transistors (DHBTs). Following her Ph.D., she performed postdoctoral research with Profs. Chenming Hu and Ali Javey at the University of California at Berkeley, investigating III-V tunneling field effect transistors (TFETs) and metal-oxide-semiconductor field effect transistors (MOSFETs). Prof. Zeng has published 31 journal papers and 16 international conference papers.

有意者请参考相关链接

<http://www.ece.udel.edu/research/by-faculty.Yuping%20Zeng.html>

<https://www.eecis.udel.edu/~yzeng/>

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